

# **Description**

The DMP2120U uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.



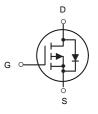
**SOT-23** 

### **General Features**

 $V_{DS} = -20V, I_{D} = -4.2A$ 

 $R_{DS(ON)} < 55 m\Omega$  V  $_{GS}$  =-4.5 V

 $R_{DS(ON)}$  < 75m  $\Omega$ @  $V_{GS}$ =-2.5V



## P-Channel MOSFET

# **Application**

PWM applications

Load switch

Power management

**Package Marking and Ordering Information** 

Product ID	Pack	Brand	Qty(PCS)
DMP2120U	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±12	V
<b>I</b> D	Drain Current-Continuous	-4.2	Α
Ірм	Drain Current-Pulsed (Note 1)	-15	Α
P <sub>D</sub>	Maximum Power Dissipation	1.7	W
Тյ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	74	°C/W



Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

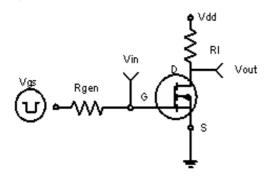
Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20	-	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μΑ	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.45	-0.7	-1.0	V	
Drain Course On Otata Basistanas	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	48	55	0	
Drain-Source On-State Resistance		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A	-	60	75	mΩ	
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4.2A	-	6	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-4V,V <sub>GS</sub> =0V, F=1.0MHz	-	740	-	PF	
Output Capacitance	C <sub>oss</sub>		-	290	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.UIVITZ	-	190	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>		-	12	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-4V, , $R_L$ =-1.2 $\Omega$ ,	-	35	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ =-4.5 $V$ , $R_g$ =1 $\Omega$	-	30	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS	
Total Gate Charge	Qg		-	7.8	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-4V,I <sub>D</sub> =-4.1A,V <sub>GS</sub> =-4.5V	-	1.2	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.6	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-4.1A	-	-	-1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-4.1	Α	

## Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

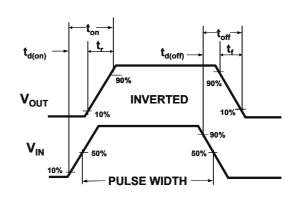
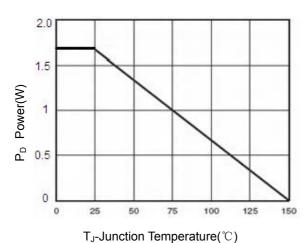


Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 

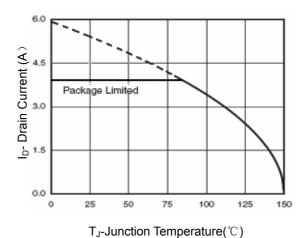
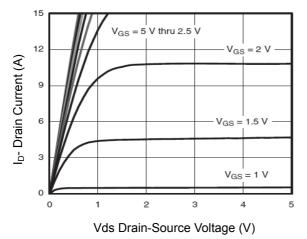


Figure 4 Drain Current



**Figure 5 Output Characteristics** 

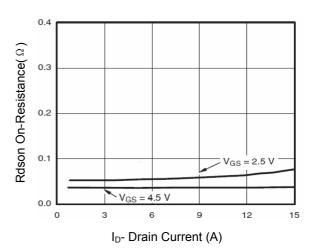
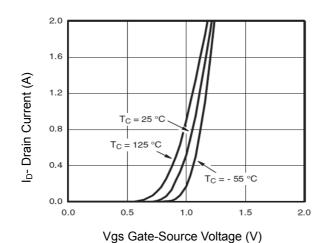
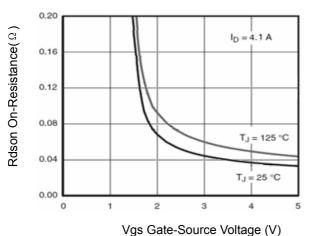


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



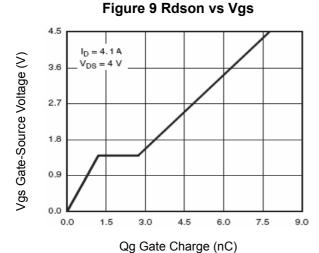


Figure 11 Gate Charge

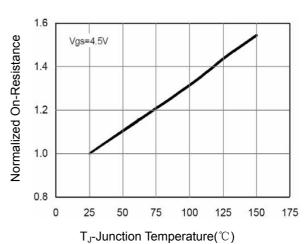
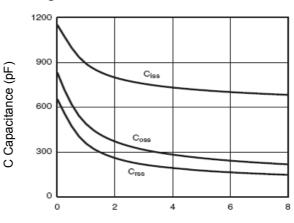
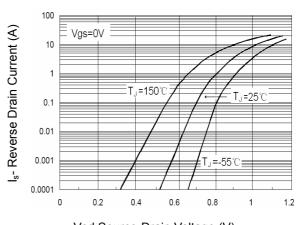


Figure 8 Drain-Source On-Resistance



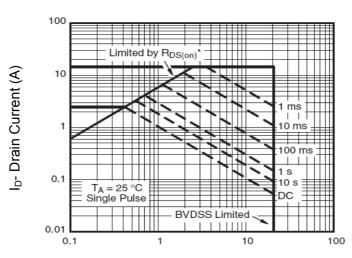
Vds Drain-Source Voltage (V) Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

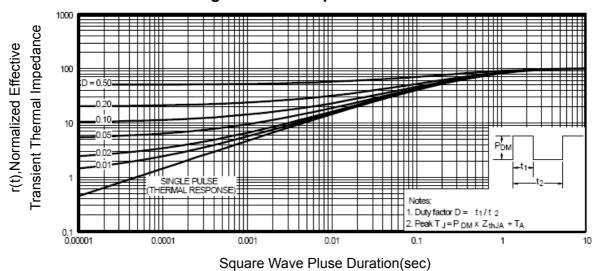
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

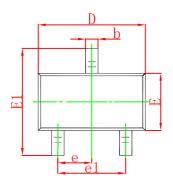
**Figure 13 Safe Operation Area** 

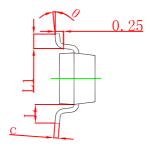


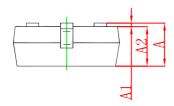
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

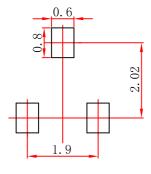






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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